

Schottky Barrier Diodes

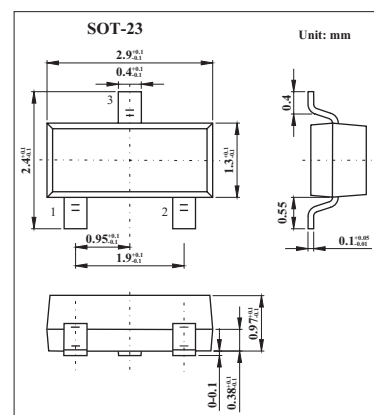
MMBD101

■ Features

- Low Noise Figure-6.0dB Typ@1.0GHz
- Very Low Capacitance-Less Than 1.0pF@zero Volts
- High Forward Conductance-0.5volts(typ)@ $I_F=10\text{mA}$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	7.0	V
Forward Power Dissipation			
@ $T_a = 25^\circ\text{C}$	pF	280	mW
Derate above 25°C		2.2	mW/ $^\circ\text{C}$
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 10\ \mu\text{A}$	7.0	10		V
Diode Capacitance	C_T	$V_R = 0, f = 1.0\text{MHz}, \text{Note 1}$		0.88	1.0	pF
Forward Voltage	V_F	$I_F = 10\text{mA}$		0.5	0.6	V
Reverse Leakage	I_R	$V_R = 3.0\text{V}$		0.02	0.25	μA

■ Marking

Marking	4M
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